

Description

N-channel MOSFET

Features

- $V_{DS}=60V$, $I_D=3A$
- $R_{DS(ON)} < 100m\Omega$ @ $V_{GS} = 10V$
 $R_{DS(ON)} < 110m\Omega$ @ $V_{GS} = 4.5V$
- High Power and Current Handling Capability
- Lead Free Product is Acquired
- Surface Mount Package

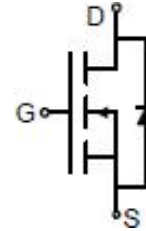
Application

- Battery Protection
- Load Switch
- Power Management

Package



SOT-23



Absolute Maximum Ratings (T_C=25°C unless otherwise specified)

Symbol	Parameter	Max.	Units
V _{DSS}	Drain-Source Voltage	60	V
V _{GSS}	Gate-Source Voltage	±20	V
I _D	Continuous Drain Current	T _C = 25°C	3
		T _C = 100°C	2
I _{DM}	Pulsed Drain Current ^{note1}	10	A
P _D	Power Dissipation	T _A = 25°C	0.35
R _{θJA}	Thermal Resistance, Junction to Ambient	357	°C/W
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C

Electrical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	60	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=48V, V_{GS}=0V,$	-	-	1	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 20V$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	-	2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance <small>note2</small>	$V_{GS}=10V, I_D=2A$	-	-	100	m Ω
		$V_{GS}=4.5V, I_D=1A$	-	-	110	
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=30V, V_{GS}=0V,$ $f=1.0MHz$	-	250	-	pF
C_{oss}	Output Capacitance		-	26	-	pF
C_{rss}	Reverse Transfer Capacitance		-	20	-	pF
Q_g	Total Gate Charge	$V_{DS}=30V, I_D=3A,$ $V_{GS}=4.5V$	-	7	-	nC
Q_{gs}	Gate-Source Charge		-	1.2	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	1.5	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD}=30V, I_D=1.5A,$ $R_{GEN}=1\Omega, V_{GS}=10V,$	-	6.5	-	ns
t_r	Turn-on Rise Time		-	15.2	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	15.2	-	ns
t_f	Turn-off Fall Time		-	10.3	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	3	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	10	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=1A$	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

 2. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

Typical Performance Characteristics

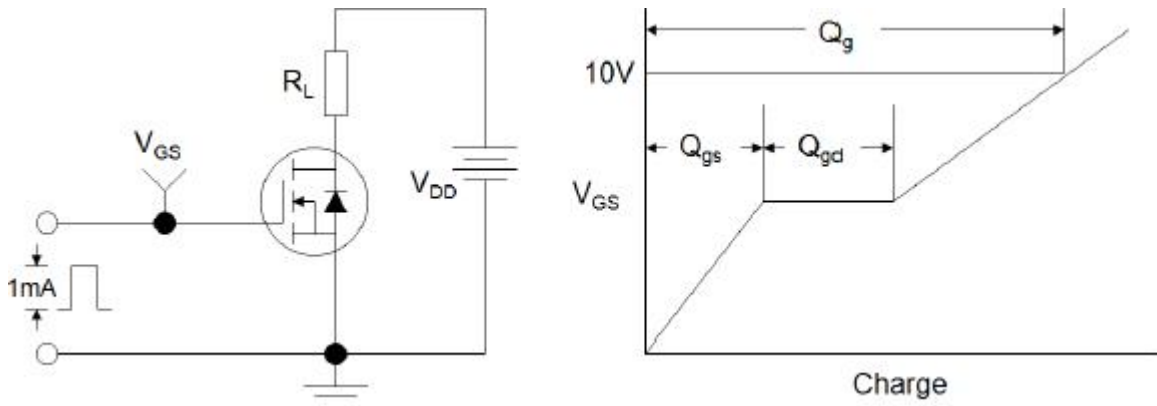


Figure1:Gate Charge Test Circuit & Waveform

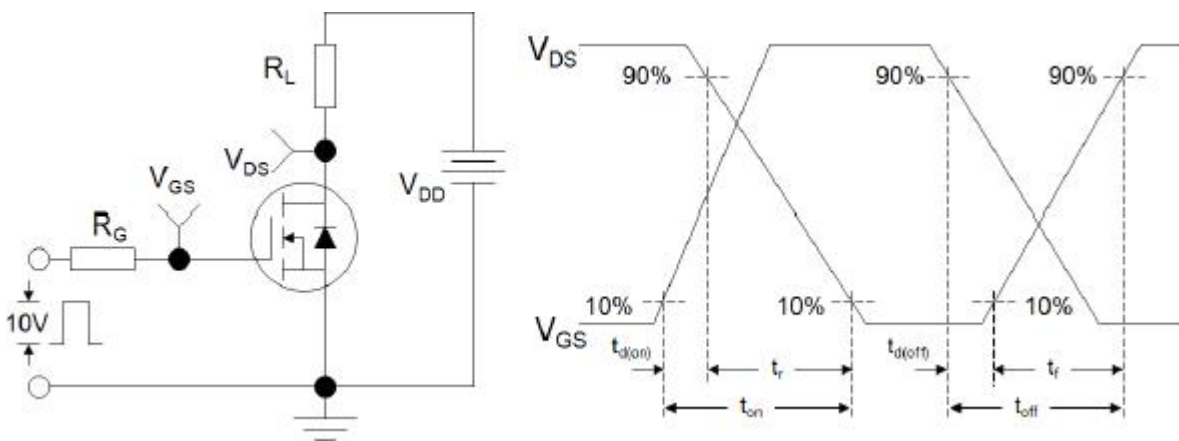


Figure 2: Resistive Switching Test Circuit & Waveforms

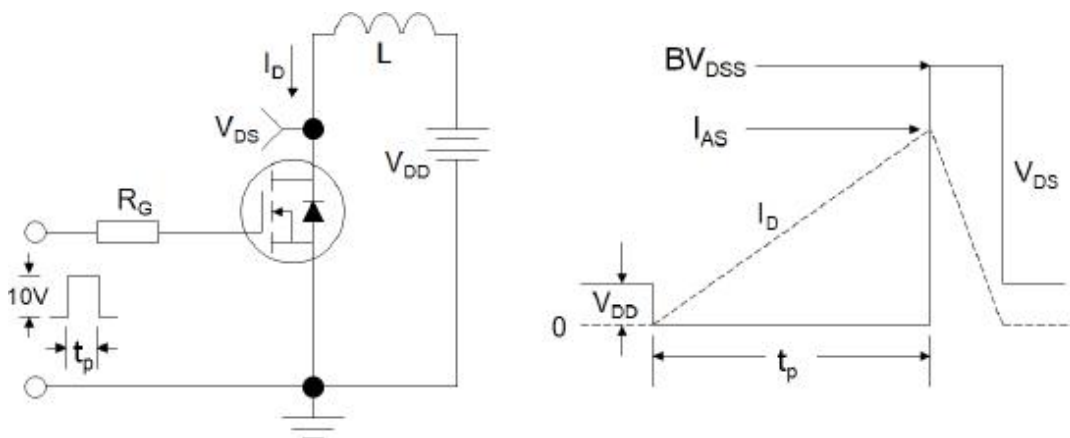


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

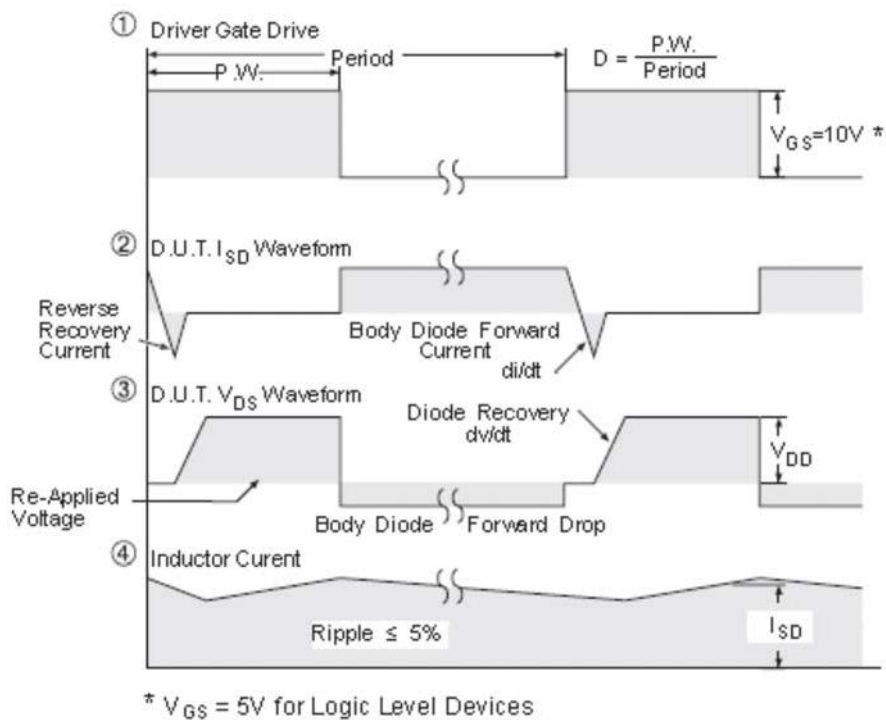
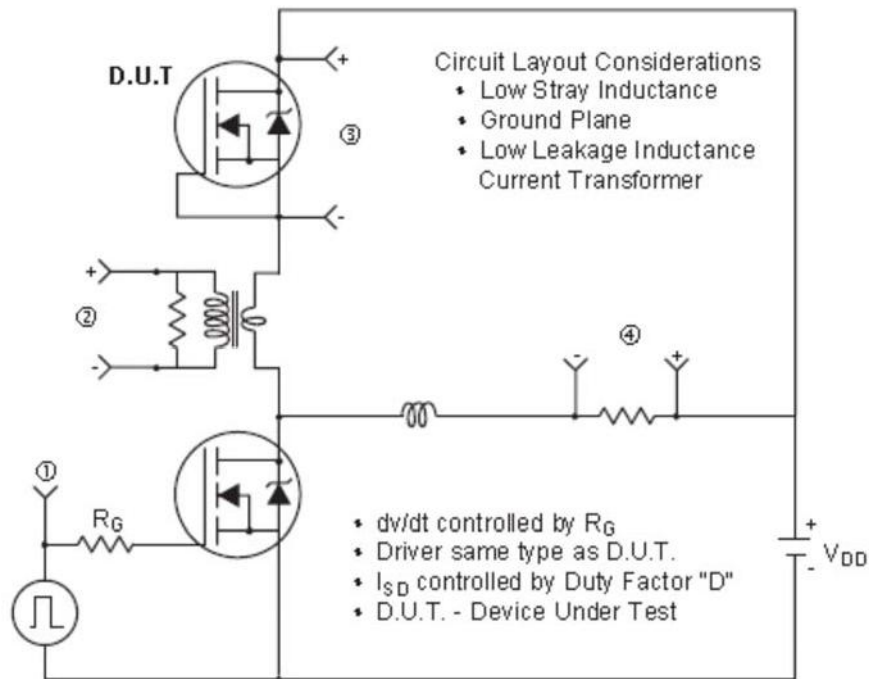
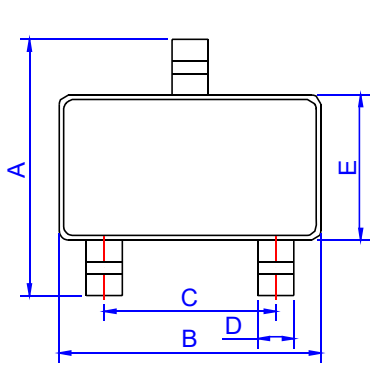
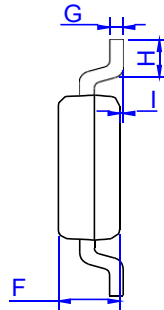


Figure 4: Peak Diode Recovery dv/dt Test Circuit & Waveforms (For N-channel)

Package Mechanical Data

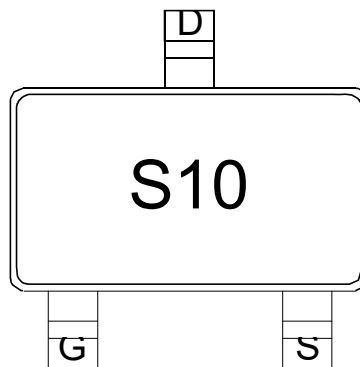


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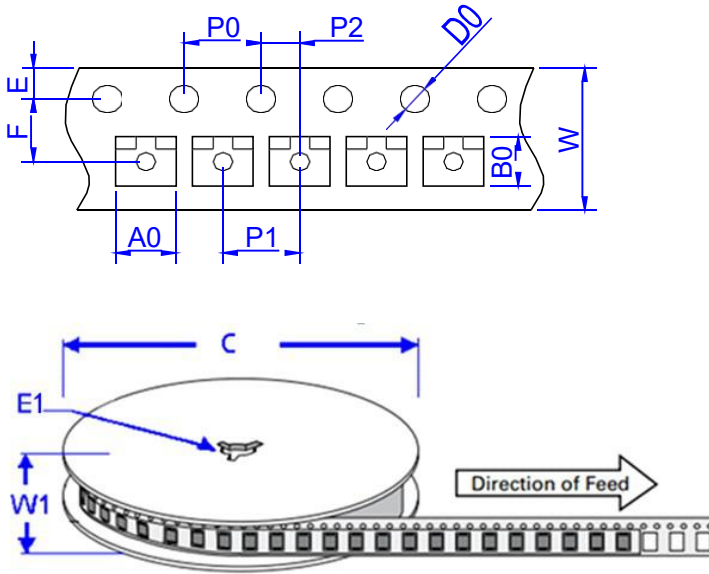
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.30	2.40	2.50	0.091	0.095	0.098
B	2.80	2.90	3.00	0.110	0.114	0.118
C	1.90 REF			0.075 REF		
D	0.35	0.40	0.45	0.014	0.016	0.018
E	1.20	1.30	1.40	0.047	0.051	0.055
F	0.90	1.00	1.10	0.035	0.039	0.043
G		0.10	0.15		0.004	0.006
H	0.20			0.008		
I	0		0.10	0		0.004

Marking



S10: Device Code

Package Information-SOT-23



Ref.	Dimensions	
	Millimeters	Inches
A0	3.15 ± 0.3	0.124 ± 0.012
B0	2.77 ± 0.3	0.109 ± 0.012
C	178	7.0
D0	1.50±0.1	0.059 ± 0.004
E	1.75 ± 0.2	0.069 ± 0.008
E1	13.3±0.3	0.524± 0.012
F	3.5 ± 0.2	0.138 ± 0.008
P0	4.00 ± 0.2	0.157 ± 0.008
P1	4.00 ± 0.2	0.157 ± 0.008
P2	2.00 ± 0.2	0.079 ± 0.008
W	8.00 ± 0.2	0.315 ± 0.008
W1	11.5±1.0	0.453 ± 0.039

Ordering Information-SOT-23

OUTLINE	PACKAGE TYPE	QUANTITY REEL	DESCRIPTION
TAPING	SOT-23	3,000pcs	7 inch reel pack